EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7580	(first or second) near3 (form$3 near3 (underly$3 layer or mask) same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:31
L2	7802	((first or second or third or fourth or fifth or sixth or seventh) near3 process) same (form$3 near3 (underly$3 layer or mask) or (bump and dip near3 transfer layer) or ((planar$3 or light absor$3 or light-emit$3 or light emit$3) near3 layer)same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:31
L3	1476	L1 and L2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:31
L4	74	L3 and ((first second third fourth fifth sixth seventh) near3 process)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/02/16 14:31
L5	4	("6495862" "20030062530" "20030218179" "20040048409").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/16 14:31
L6	0	L4 and L5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:31
L7	10	energy level same absorption near3 layer with band gap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:32

L8	7580	(first or second) near3 (form$3 near3 (underly $3 layer or mask) same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:32
L9	1	L7 and L8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:32
L10	7802	((first or second or third or fourth or fifth or sixth or seventh) near3 process) same (form$3 near3 (underly$3 layer or mask) or (bump and dip near3 transfer layer) or ((planar$3 or light absor$3 or light-emit$3 or light emit$3) near3 layer)same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:32
L11	1476	L8 and L10	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:32
L12	74	L11 and ((first second third fourth fifth sixth seventh) near3 process)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/02/16 14:32
L13	4	("6495862" "20030062530" "20030218179" "20040048409").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/16 14:32
L14	0	L12 and L13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:32
L15	1	energy level same irradiate with backside	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/16 14:32

S1	7170	(first or second) near3 (form$3 near3 (underly $3 layer or mask) same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 10:07
S2	7293	((first or second or third or fourth or fifth or sixth or seventh) near3 process) same (form$3 near3 (underly$3 layer or mask) or (bump and dip near3 transfer layer) or ((planar$3 or light absor$3 or light-emit$3 or light emit$3) near3 layer)same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 10:59
S3	1367	S1 and S2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 10:59
S4	67	S3 and ((first second third fourth fifth sixth seventh) near3 process)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/09/27 11:07
S5	7	("6495862" "20030062530" "20030218179" "20040048409").pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/27 10:58
S6	4	("6495862" "20030062530" "20030218179" "20040048409").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/27 10:58
S7	0	S4 and S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 18:05
S8	71	S4 or S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 11:06

S9	67	S8 and (((first or second or third or fourth or fifth or sixth or seventh) near3 process) same (form$3 near3 (underly $3 layer or mask) or (bump and dip near3 transfer layer) or ((planar $3 or light absor$3 or light-emit$3 or light emit $3) near3 layer)same substrate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 11:00
S10	71	S8 and (first second third fourth fifth sixth seventh process planar$3 layer form$3 microscopic plane decompos$3 transfer$3 extract$3 active substrate light absor$3 emit$3 grow$3 irradiat$3 nitride n-type p-type type semiconductor wafer sapphire GaN AlN SiC principal plane nitrogen crystal$3 groove$3 cut$3 gap energy band level impur$3 pur$3 radiat$3 non-radiat$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/27 11:15
S11	2	("20030013266").pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/27 18:05
S12	10	energy level same absorption near3 layer with band gap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/02 10:39
S13	7522	(first or second) near3 (form$3 near3 (underly $3 layer or mask) same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/02 10:40
S14	1	S12 and S13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/02 10:40

S15	7673	((first or second or third or fourth or fifth or sixth or seventh) near3 process) same (form$3 near3 (underly$3 layer or mask) or (bump and dip near3 transfer layer) or ((planar$3 or light absor$3 or light-emit$3 or light emit$3) near3 layer)same substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/02 10:41
S16	1455	S13 and S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/02 10:41
S17	71	S16 and ((first second third fourth fifth sixth seventh) near3 process)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/02/02 10:41
S18	4	("6495862" "20030062530" "20030218179" "20040048409").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/02 10:41
S19	0	S17 and S18	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/02 10:41
S20	1	energy level same irradiate with backside	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/15 22:00
S21	7	("20030013266" | "20030062530" | "20030218179" | "20040048409" | "20040096999" | "20050062125" | "6495862").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/02/15 22:02

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